

Contents

CHAPTER 1

Models for Integrated-Circuit Active Devices 1

- 1.1 Introduction 1
- 1.2 Depletion Region of a pn Junction 1
 - 1.2.1 Depletion-Region Capacitance 5
 - 1.2.2 Junction Breakdown 6
- 1.3 Large-Signal Behavior of Bipolar Transistors 8
 - 1.3.1 Large-Signal Models in the Forward-Active Region 9
 - 1.3.2 Effects of Collector Voltage on Large-Signal Characteristics in the Forward-Active Region 14
 - 1.3.3 Saturation and Inverse Active Regions 16
 - 1.3.4 Transistor Breakdown Voltages 20
 - 1.3.5 Dependence of Transistor Current Gain β_F on Operating Conditions 23
- 1.4 Small-Signal Models of Bipolar Transistors 26
 - 1.4.1 Transconductance 27
 - 1.4.2 Base-Charging Capacitance 28
 - 1.4.3 Input Resistance 29
 - 1.4.4 Output Resistance 29
 - 1.4.5 Basic Small-Signal Model of the Bipolar Transistor 30
 - 1.4.6 Collector-Base Resistance 30
 - 1.4.7 Parasitic Elements in the Small-Signal Model 31
 - 1.4.8 Specification of Transistor Frequency Response 34
- 1.5 Large Signal Behavior of Metal-Oxide-Semiconductor Field-Effect Transistors 38
 - 1.5.1 Transfer Characteristics of MOS Devices 38
 - 1.5.2 Comparison of Operating Regions of Bipolar and MOS Transistors 45
 - 1.5.3 Decomposition of Gate-Source Voltage 47
 - 1.5.4 Threshold Temperature Dependence 47
 - 1.5.5 MOS Device Voltage Limitations 48
- 1.6 Small-Signal Models of the MOS Transistors 49
 - 1.6.1 Transconductance 50
 - 1.6.2 Intrinsic Gate-Source and Gate-Drain Capacitance 51
 - 1.6.3 Input Resistance 52
 - 1.6.4 Output Resistance 52
 - 1.6.5 Basic Small-Signal Model of the MOS Transistor 52
 - 1.6.6 Body Transconductance 53
 - 1.6.7 Parasitic Elements in the Small-Signal Model 54
 - 1.6.8 MOS Transistor Frequency Response 55
- 1.7 Short-Channel Effects in MOS Transistors 58
 - 1.7.1 Velocity Saturation from the Horizontal Field 59
 - 1.7.2 Transconductance and Transition Frequency 63
 - 1.7.3 Mobility Degradation from the Vertical Field 65
- 1.8 Weak Inversion in MOS Transistors 65
 - 1.8.1 Drain Current in Weak Inversion 66
 - 1.8.2 Transconductance and Transition Frequency in Weak Inversion 68
- 1.9 Substrate Current Flow in MOS Transistors 71
 - A.1.1 Summary of Active-Device Parameters 73

CHAPTER 2**Bipolar, MOS, and BiCMOS
Integrated-Circuit Technology 78**

- 2.1 Introduction 78
- 2.2 Basic Processes in Integrated-Circuit Fabrication 79
 - 2.2.1 Electrical Resistivity of Silicon 79
 - 2.2.2 Solid-State Diffusion 80
 - 2.2.3 Electrical Properties of Diffused Layers 82
 - 2.2.4 Photolithography 84
 - 2.2.5 Epitaxial Growth 85
 - 2.2.6 Ion Implantation 87
 - 2.2.7 Local Oxidation 87
 - 2.2.8 Polysilicon Deposition 87
- 2.3 High-Voltage Bipolar Integrated-Circuit Fabrication 88
- 2.4 Advanced Bipolar Integrated-Circuit Fabrication 92
- 2.5 Active Devices in Bipolar Analog Integrated Circuits 95
 - 2.5.1 Integrated-Circuit npn Transistor 96
 - 2.5.2 Integrated-Circuit pnp Transistors 107
- 2.6 Passive Components in Bipolar Integrated Circuits 115
 - 2.6.1 Diffused Resistors 115
 - 2.6.2 Epitaxial and Epitaxial Pinch Resistors 119
 - 2.6.3 Integrated-Circuit Capacitors 120
 - 2.6.4 Zener Diodes 121
 - 2.6.5 Junction Diodes 122
- 2.7 Modifications to the Basic Bipolar Process 123
 - 2.7.1 Dielectric Isolation 123
 - 2.7.2 Compatible Processing for High-Performance Active Devices 124
 - 2.7.3 High-Performance Passive Components 127
- 2.8 MOS Integrated-Circuit Fabrication 127
- 2.9 Active Devices in MOS Integrated Circuits 131
 - 2.9.1 n-Channel Transistors 131
 - 2.9.2 p-Channel Transistors 141
 - 2.9.3 Depletion Devices 142
 - 2.9.4 Bipolar Transistors 142
- 2.10 Passive Components in MOS Technology 144
 - 2.10.1 Resistors 144
 - 2.10.2 Capacitors in MOS Technology 145
 - 2.10.3 Latchup in CMOS Technology 148
- 2.11 BiCMOS Technology 150
- 2.12 Heterojunction Bipolar Transistors 152
- 2.13 Interconnect Delay 153
- 2.14 Economics of Integrated-Circuit Fabrication 154
 - 2.14.1 Yield Considerations in Integrated-Circuit Fabrication 154
 - 2.14.2 Cost Considerations in Integrated-Circuit Fabrication 157
- 2.15 Packaging Considerations for Integrated Circuits 159
 - 2.15.1 Maximum Power Dissipation 159
 - 2.15.2 Reliability Considerations in Integrated-Circuit Packaging 162
- A.2.1 SPICE Model-Parameter Files 163

CHAPTER 3**Single-Transistor and Multiple-Transistor
Amplifiers 170**

- 3.1 Device Model Selection for Approximate Analysis of Analog Circuits 171
- 3.2 Two-Port Modeling of Amplifiers 172
- 3.3 Basic Single-Transistor Amplifier Stages 174
 - 3.3.1 Common-Emitter Configuration 175
 - 3.3.2 Common-Source Configuration 179
 - 3.3.3 Common-Base Configuration 183
 - 3.3.4 Common-Gate Configuration 186

3.3.5	Common-Base and Common-Gate Configurations with Finite r_o	188
3.3.5.1	Common-Base and Common-Gate Input Resistance	188
3.3.5.2	Common-Base and Common-Gate Output Resistance	190
3.3.6	Common-Collector Configuration (Emitter Follower)	191
3.3.7	Common-Drain Configuration (Source Follower)	195
3.3.8	Common-Emitter Amplifier with Emitter Degeneration	197
3.3.9	Common-Source Amplifier with Source Degeneration	200
3.4	Multiple-Transistor Amplifier Stages	202
3.4.1	The CC-CE, CC-CC, and Darlington Configurations	202
3.4.2	The Cascode Configuration	206
3.4.2.1	The Bipolar Cascode	206
3.4.2.2	The MOS Cascode	208
3.4.3	The Active Cascode	211
3.4.4	The Super Source Follower	213
3.5	Differential Pairs	215
3.5.1	The dc Transfer Characteristic of an Emitter-Coupled Pair	215
3.5.2	The dc Transfer Characteristic with Emitter Degeneration	217
3.5.3	The dc Transfer Characteristic of a Source-Coupled Pair	218
3.5.4	Introduction to the Small-Signal Analysis of Differential Amplifiers	221
3.5.5	Small-Signal Characteristics of Balanced Differential Amplifiers	224
3.5.6	Device Mismatch Effects in Differential Amplifiers	231
3.5.6.1	Input Offset Voltage and Current	231
3.5.6.2	Input Offset Voltage of the Emitter-Coupled Pair	232
3.5.6.3	Offset Voltage of the Emitter-Coupled Pair: Approximate Analysis	232
3.5.6.4	Offset Voltage Drift in the Emitter-Coupled Pair	234

3.5.6.5	Input Offset Current of the Emitter-Coupled Pair	235
3.5.6.6	Input Offset Voltage of the Source-Coupled Pair	236
3.5.6.7	Offset Voltage of the Source-Coupled Pair: Approximate Analysis	236
3.5.6.8	Offset Voltage Drift in the Source-Coupled Pair	238
3.5.6.9	Small-Signal Characteristics of Unbalanced Differential Amplifiers	238

A.3.1	Elementary Statistics and the Gaussian Distribution	246
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CHAPTER 4

Current Mirrors, Active Loads, and References 253

4.1	Introduction	253
4.2	Current Mirrors	253
4.2.1	General Properties	253
4.2.2	Simple Current Mirror	255
4.2.2.1	Bipolar	255
4.2.2.2	MOS	257
4.2.3	Simple Current Mirror with Beta Helper	260
4.2.3.1	Bipolar	260
4.2.3.2	MOS	262
4.2.4	Simple Current Mirror with Degeneration	262
4.2.4.1	Bipolar	262
4.2.4.2	MOS	263
4.2.5	Cascode Current Mirror	263
4.2.5.1	Bipolar	263
4.2.5.2	MOS	266
4.2.6	Wilson Current Mirror	274
4.2.6.1	Bipolar	274
4.2.6.2	MOS	277
4.3	Active Loads	278
4.3.1	Motivation	278
4.3.2	Common-Emitter/Common-Source Amplifier with Complementary Load	279
4.3.3	Common-Emitter/Common-Source Amplifier with Depletion Load	282

- 4.3.4 Common-Emitter/Common-Source Amplifier with Diode-Connected Load 284
- 4.3.5 Differential Pair with Current-Mirror Load 287
 - 4.3.5.1 Large-Signal Analysis 287
 - 4.3.5.2 Small-Signal Analysis 288
 - 4.3.5.3 Common-Mode Rejection Ratio 293
- 4.4 Voltage and Current References 299
 - 4.4.1 Low-Current Biasing 299
 - 4.4.1.1 Bipolar Widlar Current Source 299
 - 4.4.1.2 MOS Widlar Current Source 302
 - 4.4.1.3 Bipolar Peaking Current Source 303
 - 4.4.1.4 MOS Peaking Current Source 304
 - 4.4.2 Supply-Insensitive Biasing 306
 - 4.4.2.1 Widlar Current Sources 306
 - 4.4.2.2 Current Sources Using Other Voltage Standards 307
 - 4.4.2.3 Self Biasing 309
 - 4.4.3 Temperature-Insensitive Biasing 317
 - 4.4.3.1 Band-Gap-Referenced Bias Circuits in Bipolar Technology 317
 - 4.4.3.2 Band-Gap-Referenced Bias Circuits in CMOS Technology 323
- A.4.1 Matching Considerations in Current Mirrors 327
 - A.4.1.1 Bipolar 327
 - A.4.1.2 MOS 329
- A.4.2 Input Offset Voltage of Differential Pair with Active Load 332
 - A.4.2.1 Bipolar 332
 - A.4.2.2 MOS 334
- 5.2 The Emitter Follower As an Output Stage 344
 - 5.2.1 Transfer Characteristics of the Emitter-Follower 344
 - 5.2.2 Power Output and Efficiency 347
 - 5.2.3 Emitter-Follower Drive Requirements 354
 - 5.2.4 Small-Signal Properties of the Emitter Follower 355
- 5.3 The Source Follower As an Output Stage 356
 - 5.3.1 Transfer Characteristics of the Source Follower 356
 - 5.3.2 Distortion in the Source Follower 358
- 5.4 Class B Push–Pull Output Stage 362
 - 5.4.1 Transfer Characteristic of the Class B Stage 363
 - 5.4.2 Power Output and Efficiency of the Class B Stage 365
 - 5.4.3 Practical Realizations of Class B Complementary Output Stages 369
 - 5.4.4 All-*n*p*n* Class B Output Stage 376
 - 5.4.5 Quasi-Complementary Output Stages 379
 - 5.4.6 Overload Protection 380
- 5.5 CMOS Class AB Output Stages 382
 - 5.5.1 Common-Drain Configuration 383
 - 5.5.2 Common-Source Configuration with Error Amplifiers 384
 - 5.5.3 Alternative Configurations 391
 - 5.5.3.1 Combined Common-Drain Common-Source Configuration 391
 - 5.5.3.2 Combined Common-Drain Common-Source Configuration with High Swing 393
 - 5.5.3.3 Parallel Common-Source Configuration 394

CHAPTER 5

Output Stages 344

5.1 Introduction 344

CHAPTER 6

Operational Amplifiers with Single-Ended Outputs 404

6.1 Applications of Operational Amplifiers 405

- 6.1.1 Basic Feedback Concepts 405
 - 6.1.2 Inverting Amplifier 406
 - 6.1.3 Noninverting Amplifier 408
 - 6.1.4 Differential Amplifier 408
 - 6.1.5 Nonlinear Analog Operations 409
 - 6.1.6 Integrator, Differentiator 410
 - 6.1.7 Internal Amplifiers 411
 - 6.1.7.1 Switched-Capacitor Amplifier 411
 - 6.1.7.2 Switched-Capacitor Integrator 416
 - 6.2 Deviations from Ideality in Real Operational Amplifiers 419
 - 6.2.1 Input Bias Current 419
 - 6.2.2 Input Offset Current 420
 - 6.2.3 Input Offset Voltage 421
 - 6.2.4 Common-Mode Input Range 421
 - 6.2.5 Common-Mode Rejection Ratio (CMRR) 421
 - 6.2.6 Power-Supply Rejection Ratio (PSRR) 422
 - 6.2.7 Input Resistance 424
 - 6.2.8 Output Resistance 424
 - 6.2.9 Frequency Response 424
 - 6.2.10 Operational-Amplifier Equivalent Circuit 424
 - 6.3 Basic Two-Stage MOS Operational Amplifiers 425
 - 6.3.1 Input Resistance, Output Resistance, and Open-Circuit Voltage Gain 426
 - 6.3.2 Output Swing 428
 - 6.3.3 Input Offset Voltage 428
 - 6.3.4 Common-Mode Rejection Ratio 431
 - 6.3.5 Common-Mode Input Range 432
 - 6.3.6 Power-Supply Rejection Ratio (PSRR) 434
 - 6.3.7 Effect of Overdrive Voltages 439
 - 6.3.8 Layout Considerations 439
 - 6.4 Two-Stage MOS Operational Amplifiers with Cascodes 442
 - 6.5 MOS Telescopic-Cascode Operational Amplifiers 444
 - 6.6 MOS Folded-Cascode Operational Amplifiers 446
 - 6.7 MOS Active-Cascode Operational Amplifiers 450
 - 6.8 Bipolar Operational Amplifiers 453
 - 6.8.1 The dc Analysis of the 741 Operational Amplifier 456
 - 6.8.2 Small-Signal Analysis of the 741 Operational Amplifier 461
 - 6.8.3 Input Offset Voltage, Input Offset Current, and Common-Mode Rejection Ratio of the 741 470
 - 6.9 Design Considerations for Bipolar Monolithic Operational Amplifiers 472
 - 6.9.1 Design of Low-Drift Operational Amplifiers 474
 - 6.9.2 Design of Low-Input-Current Operational Amplifiers 476
- CHAPTER 7**
Frequency Response of Integrated Circuits 488
- 7.1 Introduction 488
 - 7.2 Single-Stage Amplifiers 488
 - 7.2.1 Single-Stage Voltage Amplifiers and The Miller Effect 488
 - 7.2.1.1 The Bipolar Differential Amplifier: Differential-Mode Gain 493
 - 7.2.1.2 The MOS Differential Amplifier: Differential-Mode Gain 496
 - 7.2.2 Frequency Response of the Common-Mode Gain for a Differential Amplifier 499
 - 7.2.3 Frequency Response of Voltage Buffers 502
 - 7.2.3.1 Frequency Response of the Emitter Follower 503
 - 7.2.3.2 Frequency Response of the Source Follower 509
 - 7.2.4 Frequency Response of Current Buffers 511
 - 7.2.4.1 Common-Base-Amplifier Frequency Response 514
 - 7.2.4.2 Common-Gate-Amplifier Frequency Response 515

- 7.3 Multistage Amplifier Frequency Response 516
 - 7.3.1 Dominant-Pole Approximation 516
 - 7.3.2 Zero-Value Time Constant Analysis 517
 - 7.3.3 Cascode Voltage-Amplifier Frequency Response 522
 - 7.3.4 Cascode Frequency Response 525
 - 7.3.5 Frequency Response of a Current Mirror Loading a Differential Pair 532
 - 7.3.6 Short-Circuit Time Constants 533
- 7.4 Analysis of the Frequency Response of the 741 Op Amp 537
 - 7.4.1 High-Frequency Equivalent Circuit of the 741 537
 - 7.4.2 Calculation of the -3 -dB Frequency of the 741 538
 - 7.4.3 Nondominant Poles of the 741 540
- 7.5 Relation Between Frequency Response and Time Response 542

CHAPTER 8

Feedback 553

- 8.1 Ideal Feedback Equation 553
- 8.2 Gain Sensitivity 555
- 8.3 Effect of Negative Feedback on Distortion 555
- 8.4 Feedback Configurations 557
 - 8.4.1 Series-Shunt Feedback 557
 - 8.4.2 Shunt-Shunt Feedback 560
 - 8.4.3 Shunt-Series Feedback 561
 - 8.4.4 Series-Series Feedback 562
- 8.5 Practical Configurations and the Effect of Loading 563
 - 8.5.1 Shunt-Shunt Feedback 563
 - 8.5.2 Series-Series Feedback 569
 - 8.5.3 Series-Shunt Feedback 579
 - 8.5.4 Shunt-Series Feedback 583
 - 8.5.5 Summary 587
- 8.6 Single-Stage Feedback 587
 - 8.6.1 Local Series Feedback 587

- 8.6.2 Local Shunt Feedback 591
- 8.7 The Voltage Regulator as a Feedback Circuit 593
- 8.8 Feedback Circuit Analysis Using Return Ratio 599
 - 8.8.1 Closed-Loop Gain Using Return Ratio 601
 - 8.8.2 Closed-Loop Impedance Formula Using Return Ratio 607
 - 8.8.3 Summary—Return-Ratio Analysis 612
- 8.9 Modeling Input and Output Ports in Feedback Circuits 613

CHAPTER 9

Frequency Response and Stability of Feedback Amplifiers 624

- 9.1 Introduction 624
- 9.2 Relation Between Gain and Bandwidth in Feedback Amplifiers 624
- 9.3 Instability and the Nyquist Criterion 626
- 9.4 Compensation 633
 - 9.4.1 Theory of Compensation 633
 - 9.4.2 Methods of Compensation 637
 - 9.4.3 Two-Stage MOS Amplifier Compensation 644
 - 9.4.4 Compensation of Single-Stage CMOS OP Amps 652
 - 9.4.5 Nested Miller Compensation 656
- 9.5 Root-Locus Techniques 664
 - 9.5.1 Root Locus for a Three-Pole Transfer Function 664
 - 9.5.2 Rules for Root-Locus Construction 667
 - 9.5.3 Root Locus for Dominant-Pole Compensation 675
 - 9.5.4 Root Locus for Feedback-Zero Compensation 676
- 9.6 Slew Rate 680
 - 9.6.1 Origin of Slew-Rate Limitations 680
 - 9.6.2 Methods of Improving Slew-Rate 684

- 9.6.3 Improving Slew-Rate in Bipolar Op Amps 685
- 9.6.4 Improving Slew-Rate in MOS Op Amps 686
- 9.6.5 Effect of Slew-Rate Limitations on Large-Signal Sinusoidal Performance 690
- A.9.1 Analysis in Terms of Return-Ratio Parameters 691
- A.9.2 Roots of a Quadratic Equation 692

CHAPTER 10

Nonlinear Analog Circuits 702

- 10.1 Introduction 702
- 10.2 Precision Rectification 702
- 10.3 Analog Multipliers Employing the Bipolar Transistor 708
 - 10.3.1 The Emitter-Coupled Pair as a Simple Multiplier 708
 - 10.3.2 The dc Analysis of the Gilbert Multiplier Cell 710
 - 10.3.3 The Gilbert Cell as an Analog Multiplier 712
 - 10.3.4 A Complete Analog Multiplier 715
 - 10.3.5 The Gilbert Multiplier Cell as a Balanced Modulator and Phase Detector 716
- 10.4 Phase-Locked Loops (PLL) 720
 - 10.4.1 Phase-Locked Loop Concepts 720
 - 10.4.2 The Phase-Locked Loop in the Locked Condition 722
 - 10.4.3 Integrated-Circuit Phase-Locked Loops 731
 - 10.4.4 Analysis of the 560B Monolithic Phase-Locked Loop 735
- 10.5 Nonlinear Function Symbols 743

CHAPTER 11

Noise in Integrated Circuits 748

- 11.1 Introduction 748
- 11.2 Sources of Noise 748

- 11.2.1 Shot Noise 748
- 11.2.2 Thermal Noise 752
- 11.2.3 Flicker Noise ($1/f$ Noise) 753
- 11.2.4 Burst Noise (*Popcorn Noise*) 754
- 11.2.5 Avalanche Noise 755
- 11.3 Noise Models of Integrated-Circuit Components 756
 - 11.3.1 Junction Diode 756
 - 11.3.2 Bipolar Transistor 757
 - 11.3.3 MOS Transistor 758
 - 11.3.4 Resistors 759
 - 11.3.5 Capacitors and Inductors 759
- 11.4 Circuit Noise Calculations 760
 - 11.4.1 Bipolar Transistor Noise Performance 762
 - 11.4.2 Equivalent Input Noise and the Minimum Detectable Signal 766
- 11.5 Equivalent Input Noise Generators 768
 - 11.5.1 Bipolar Transistor Noise Generators 768
 - 11.5.2 MOS Transistor Noise Generators 773
- 11.6 Effect of Feedback on Noise Performance 776
 - 11.6.1 Effect of Ideal Feedback on Noise Performance 776
 - 11.6.2 Effect of Practical Feedback on Noise Performance 776
- 11.7 Noise Performance of Other Transistor Configurations 783
 - 11.7.1 Common-Base Stage Noise Performance 783
 - 11.7.2 Emitter-Follower Noise Performance 784
 - 11.7.3 Differential-Pair Noise Performance 785
- 11.8 Noise in Operational Amplifiers 788
- 11.9 Noise Bandwidth 794
- 11.10 Noise Figure and Noise Temperature 799
 - 11.10.1 Noise Figure 799
 - 11.10.2 Noise Temperature 802

CHAPTER 12**Fully Differential Operational Amplifiers**

808

- 12.1 Introduction 808
- 12.2 Properties of Fully Differential Amplifiers 808
- 12.3 Small-Signal Models for Balanced Differential Amplifiers 811
- 12.4 Common-Mode Feedback 816
 - 12.4.1 Common-Mode Feedback at Low Frequencies 817
 - 12.4.2 Stability and Compensation Considerations in a CMFB Loop 822
- 12.5 CMFB Circuits 823
 - 12.5.1 CMFB Using Resistive Divider and Amplifier 824
 - 12.5.2 CMFB Using Two Differential Pairs 828
 - 12.5.3 CMFB Using Transistors in the Triode Region 830
 - 12.5.4 Switched-Capacitor CMFB 832
- 12.6 Fully Differential Op Amps 835
 - 12.6.1 A Fully Differential Two-Stage Op Amp 835
 - 12.6.2 Fully Differential Telescopic Cascode Op Amp 845
 - 12.6.3 Fully Differential Folded-Cascode Op Amp 846
 - 12.6.4 A Differential Op Amp with Two Differential Input Stages 847
 - 12.6.5 Neutralization 849
- 12.7 Unbalanced Fully Differential Circuits 850
- 12.8 Bandwidth of the CMFB Loop 856

Index 865